NSN 5961-01-081-0332

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-081-0332 **Inclosure Material:** Glass and plastic **Overall Length:** 0.275 inches **Overall Height:** 0.070 inches **Overall Width:** 0.260 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-86 **Component Name And Quantity:** 4 transistor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 80.0 collector to base voltage, dc all transistor and 80.0 collector to emitter voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 600.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 14 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** No